

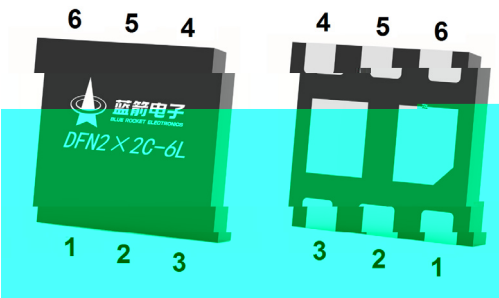
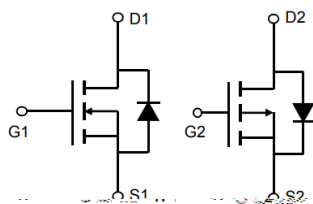
/ Descriptions

Complementary Enhancement MOSFET in a DFN2 2C-6L Plastic Package.

/ Features

N-channel	P-channel
$V_{DS(V)}=16V$	$V_{DS(V)}=-16V$
$I_D=8.4A$	$I_D=-6.3A$
$R_{DS(ON)}@4.5V\ 15m\ (Typ.13mR)$	$R_{DS(ON)}@-4.5V\ 25m\ (Typ.21mR)$
$R_{DS(ON)}@2.5V\ 18m\ (Typ.16mR)$	$R_{DS(ON)}@-2.5V\ 35m\ (Typ.28mR))$
HF Product.	

Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.



出脚	定义
PIN 1	S1
PIN 2	G1
PIN 3	D2
PIN 4	S2
PIN 5	G2
PIN 6	D1

See Marking Instructions.

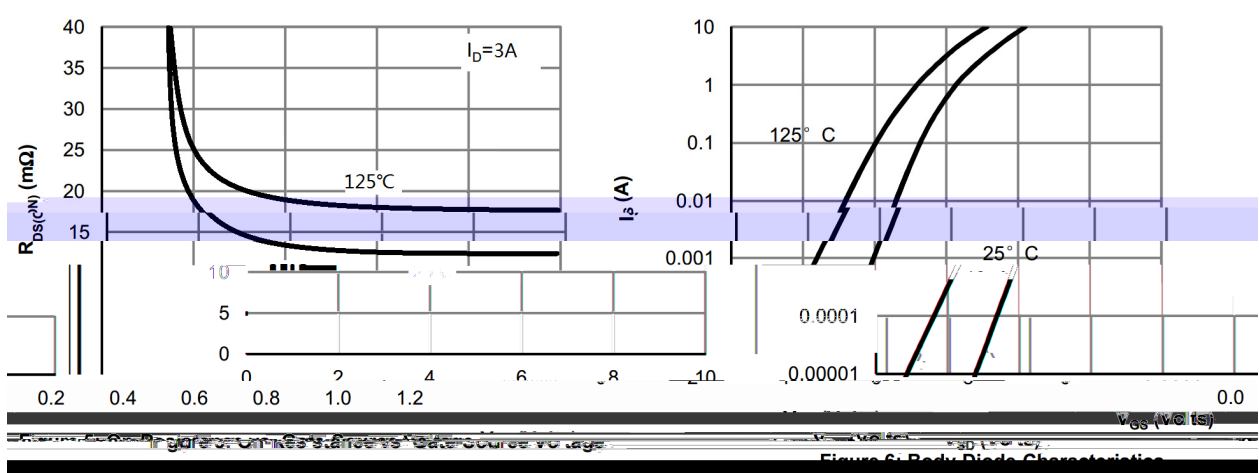
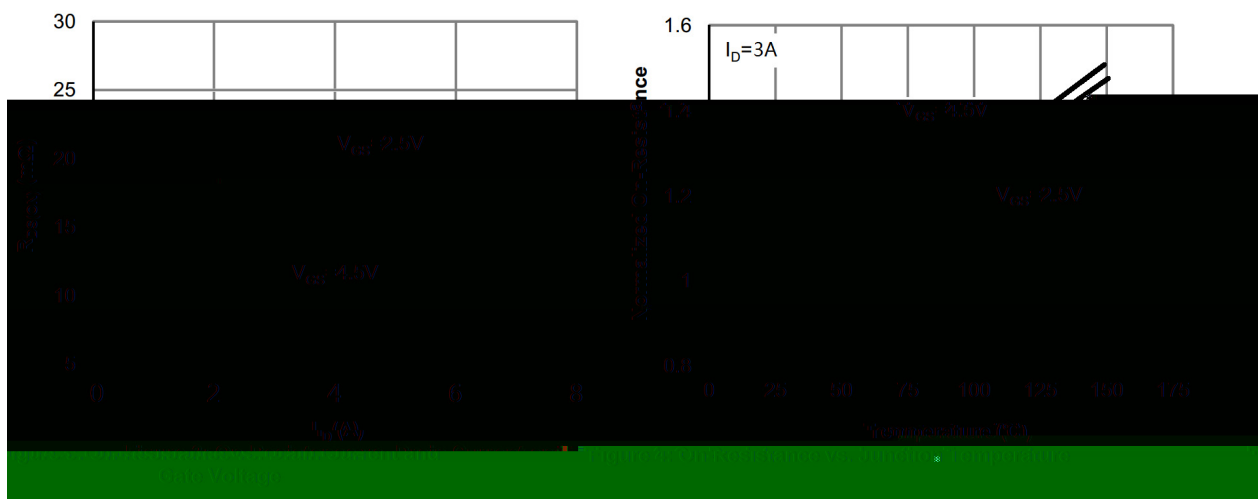
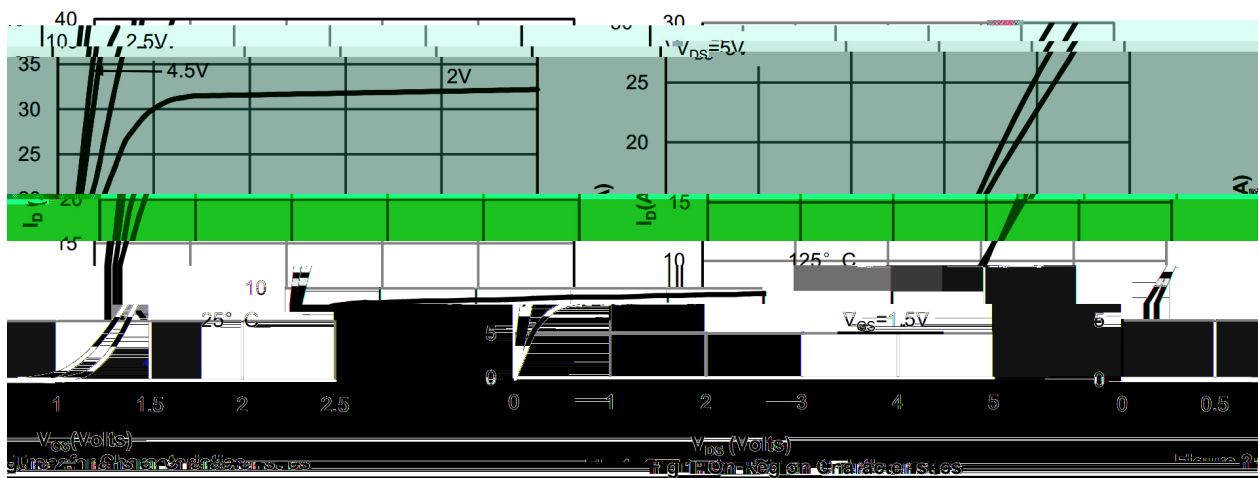
/ Absolute Maximum Ratings($T_a=25^\circ\text{C}$)

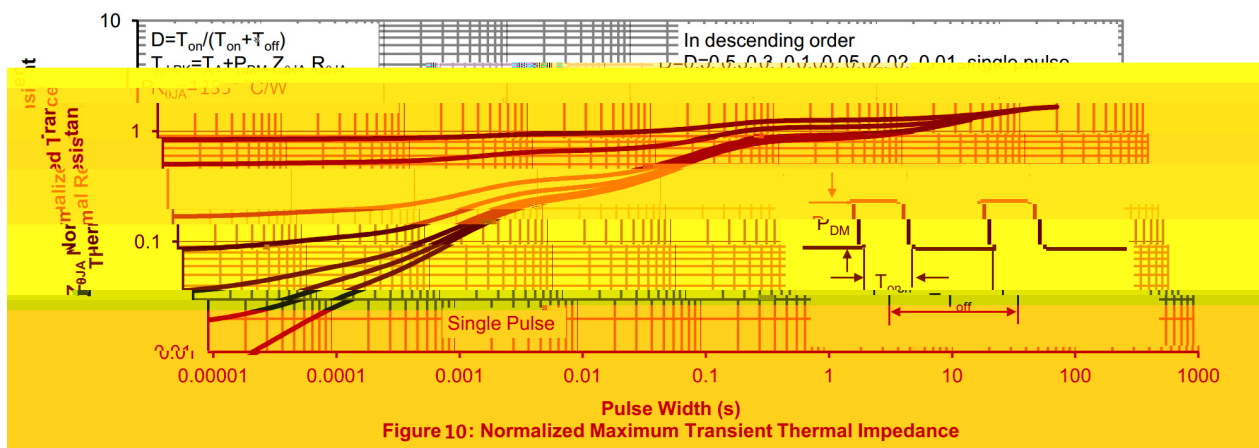
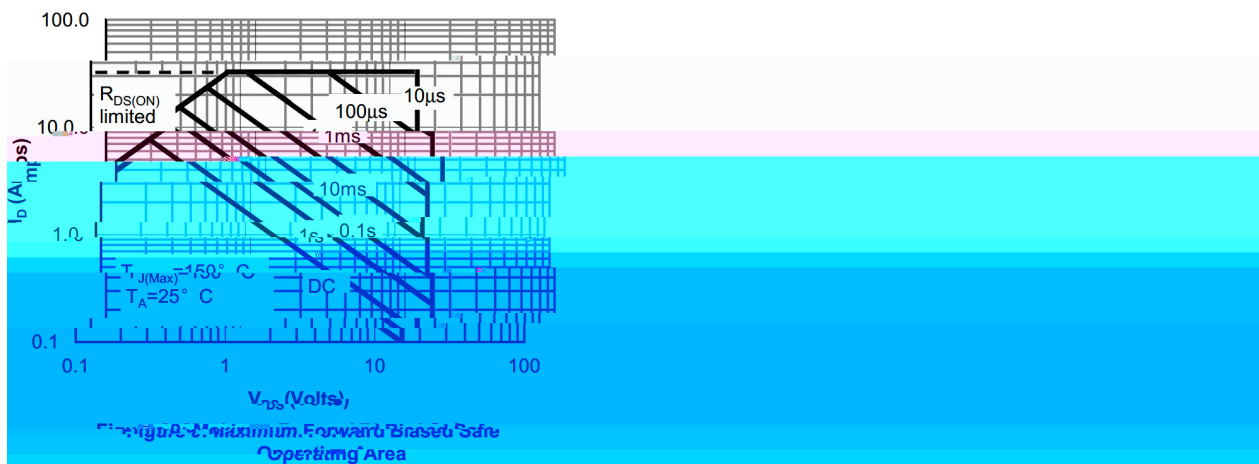
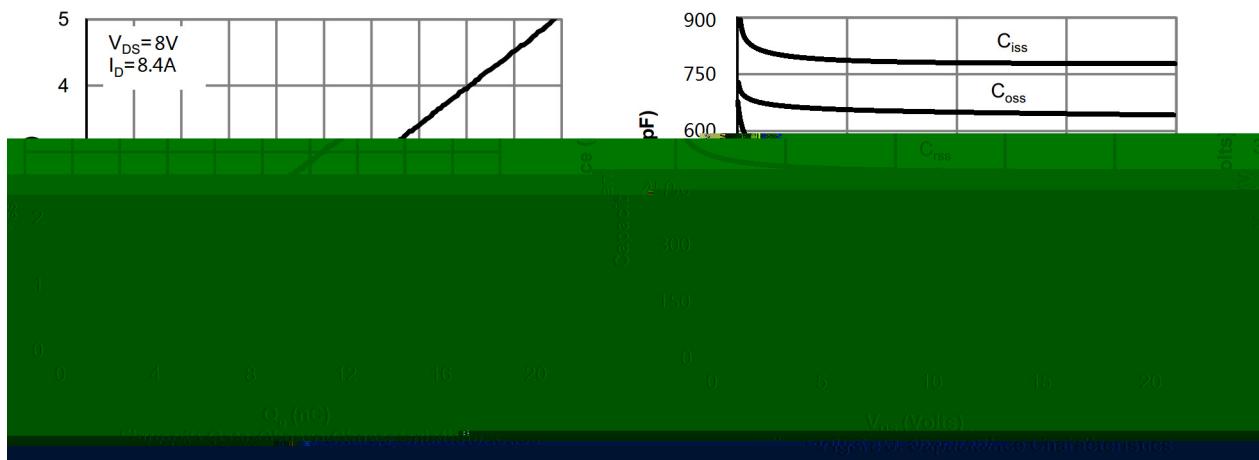
Parameter	Symbol	Rating		Unit
		N-channe	P-channell	
Drain-Source Voltage	V _{DSS}	±16		V
Gate-Source Voltage	V _{GSS}	±10		V
Continuous Drain Current	I _D	8.4	-6.3	A
Pulsed Drain Current	I _{DM}	33	-24.5	A
Avalanche Current(L=0.1mH)	I _{AS}	7	14	A
Avalanche energy(L=0.1mH)	E _{AS}	6.5	26	mJ
Power Dissipation	P _D	1.6	1.5	W
Junction and Storage Temperature Range	T _J ,T _{STG}	-55 to +150		
Maximum Junction-to-Ambient	R _{θJA} (t≤10s)	78	83	/W
	R _{θJA} (Steady-State)	135		

N- N-CHANNEL Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250 A$	16	21		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V$ $V_{GS}=0V$			1.0	A
Gate-Body leakage current	I_{GSS}	$V_{GS}=\pm 10V$ $V_{DS}=0V$			100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250 A$	0.45	0.75	0.95	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V$ $I_D=3A$		13	15	m
		$V_{GS}=2.5V$ $I_D=2A$		16	18	m
Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1.0A$			1.2	V
Input Capacitance	C_{iss}	$V_{DS}=10V$ $V_{GS}=0V$ $f=1.0MHz$		765		pF
Output Capacitance	C_{oss}			650		pF
Reverse Transfer Capacitance	C_{rss}			520		pF
Gate resistance	R_g	$V_{DS}=0V$ $V_{GS}=0V$ $f=1.0MHz$		3.5		
Total Gate Charge	Q_g	$V_{GS}=4.5V$ $V_{DS}=8.0V$ $I_D=8.4A$		17.9		nC
Gate-Source Charge	Q_{gs}			1.5		nC
Gate-Drain Charge	Q_{gd}			4.7		nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=8.0V$ $V_{GS}=10V$ $R_L=1.2$ $R_{GEN}=3$		2.5		ns
Turn-On Rise Time	t_r			7.2		ns
Turn-Off Delay Time	$t_{d(off)}$			49		ns
Turn-Off Fall Time	t_f			10.8		ns

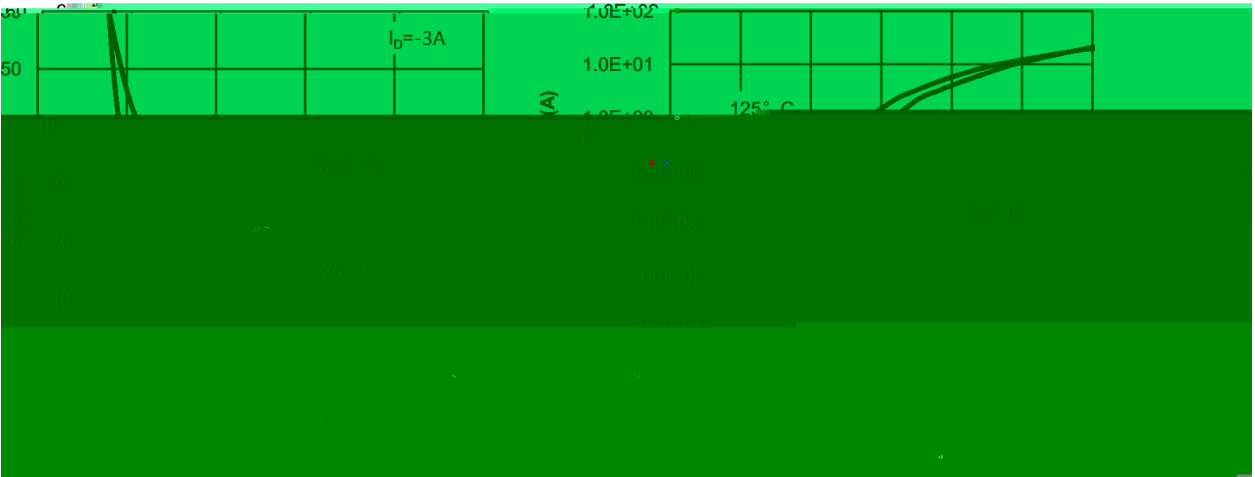
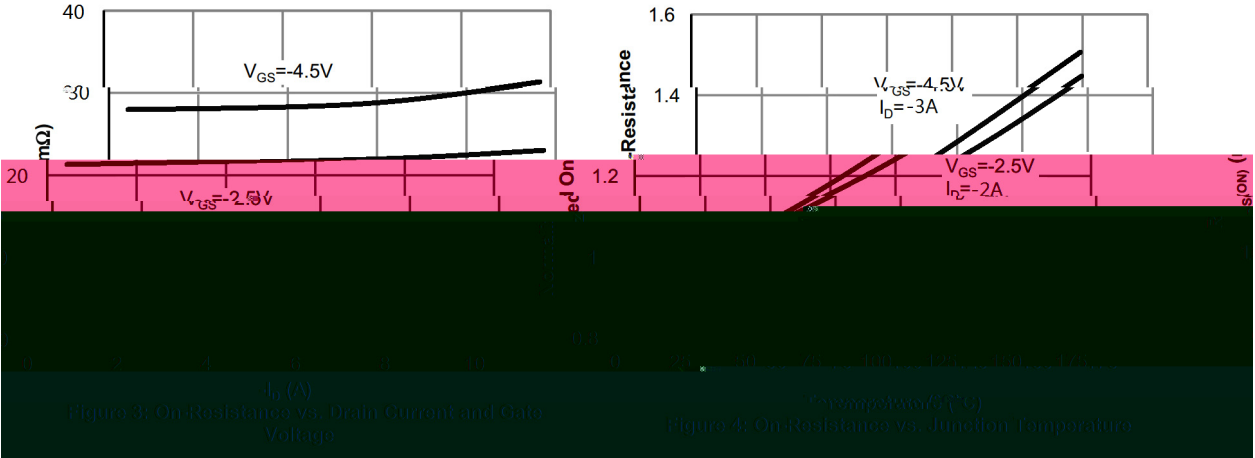
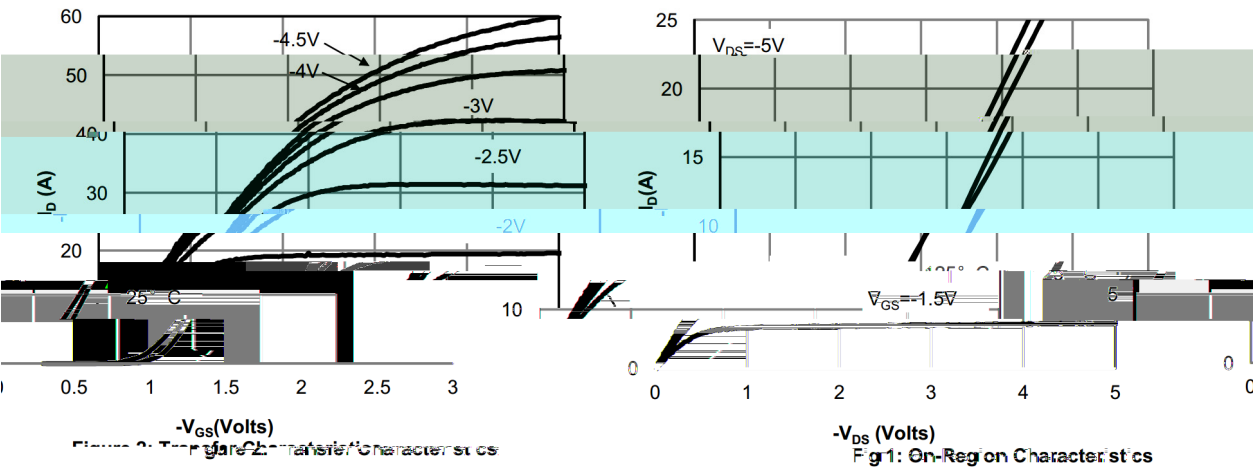
N- / N-CHANNEL Electrical Characteristic Curve



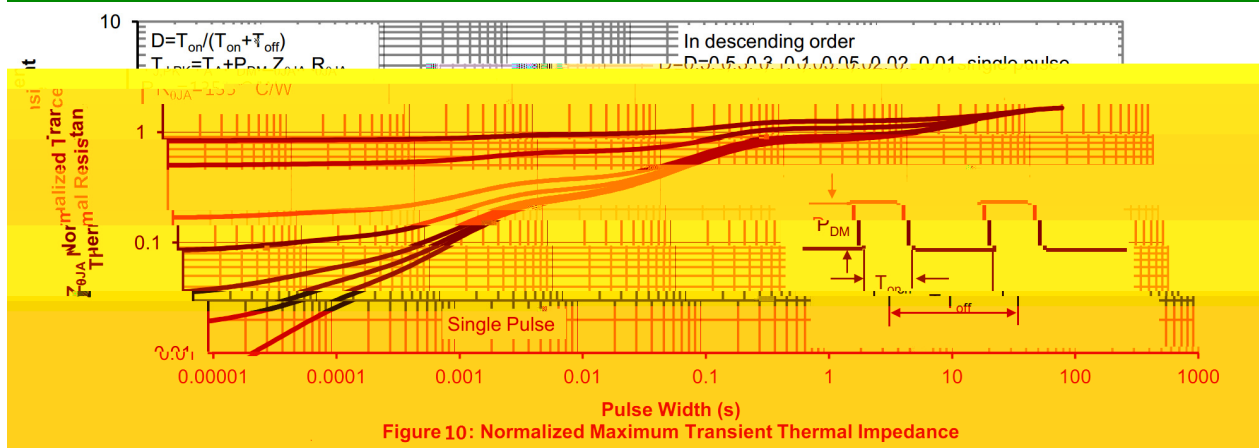
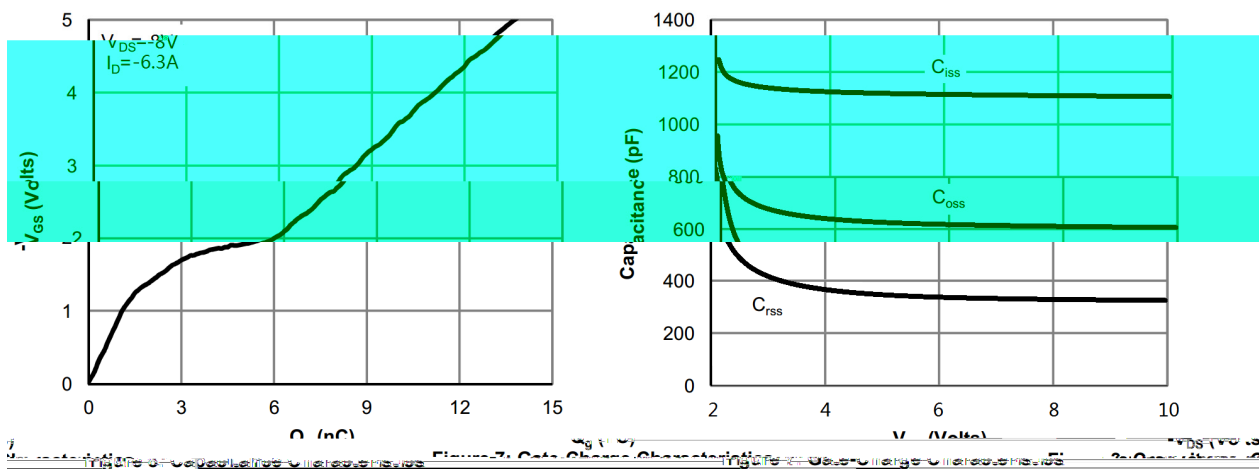
N- / N-CHANNEL Electrical Characteristic Curve


Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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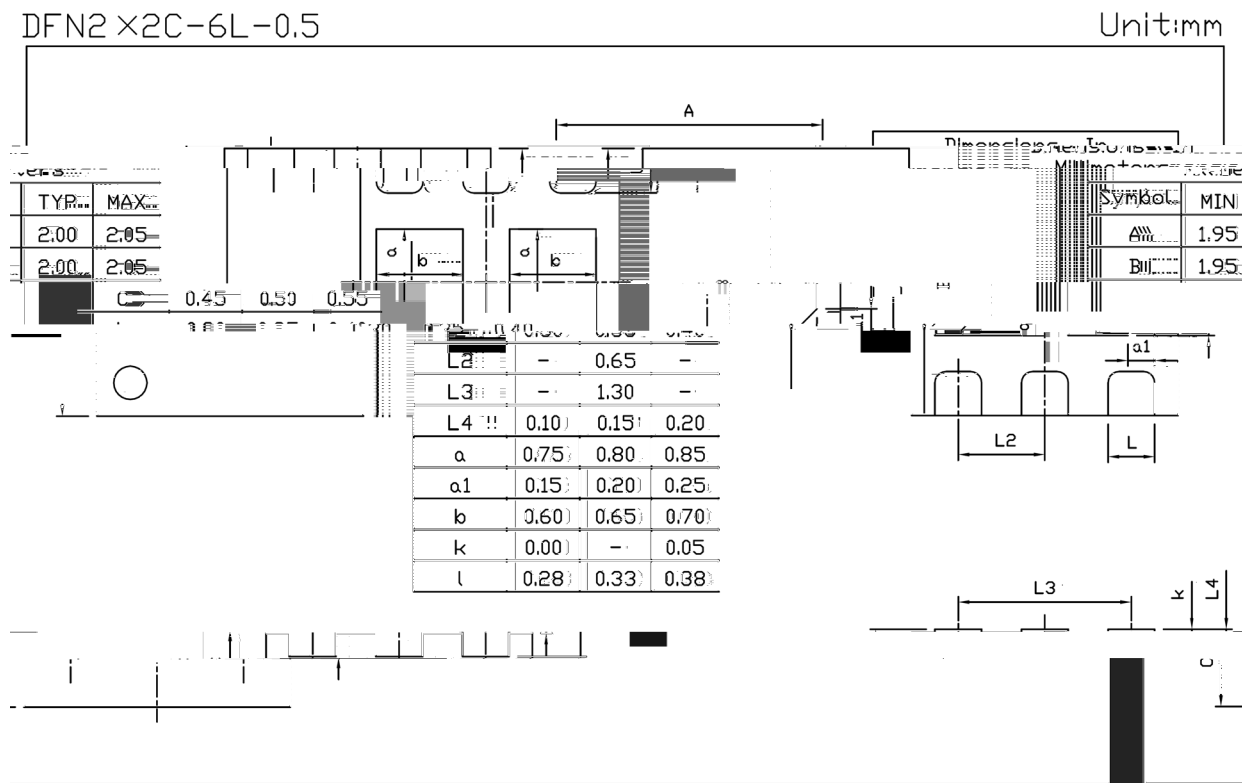
P- / P-CHANNEL Electrical Characteristic Curve



P- / P-CHANNEL Electrical Characteristic Curve



/ Package Dimensions



Rev.00 202204

/ Marking Instructions



BR

150C016

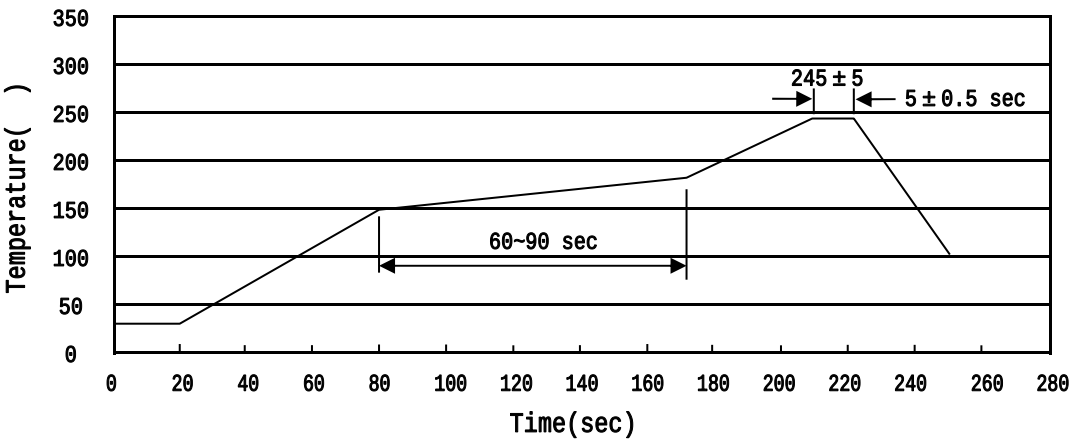
Note:

BR: Company Code

150C016: Product Type

****: Lot No. Code, code change with Lot No

() /



Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245 5

5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
DFN 2×2C-6L	4,000	10	40,000	4	160,000	7 ×8	210×205×205	445×435×230

/ Notices